

## Claims

1-4."canceled".

5."new". A transistor comprising on both sides of a lightly doped silicon monocrystal substrate having a donor concentration of about  $10^{14}$  cm.<sup>-3</sup>:  
an epitaxial layer having a donor concentration of about  $10^{17}$  cm.<sup>-3</sup>,  
wherein elements of a bipolar static induction transistor: a p<sup>+</sup> gate, n<sup>+</sup> sources and n-channels are disposed;

one channel of a multielement structure is thicker than the other normally-off channels.

6."new. The transistor according to claim 5 wherein a layer of a doped n<sup>+</sup> type polysilicon is disposed on the silicon monocrystal surface on both sides of said substrate.

7."new". A transistor comprising on both sides of a lightly doped silicon monocrystal substrate having a donor concentration of about  $10^{14}$  cm.<sup>-3</sup>:  
an epitaxial layer having a donor concentration of about  $10^{17}$  cm.<sup>-3</sup>,  
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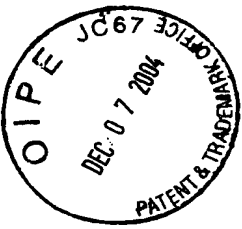
said channel is connected to a separate electrode.

8."new. The transistor according to claim 7 wherein a layer of a doped n<sup>+</sup> type polysilicon is disposed on the silicon monocrystal surface on both sides of said substrate.

AUTHOR:

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12.05.2004

EDLIN S.D.



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